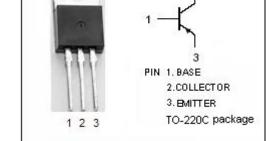


# **ISC Silicon PNP Power Transistor**

### **DESCRIPTION**

- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub>= -100V(Min)
- · High DC Current Gain-
  - :  $h_{FE}$ = 100(Min)@ ( $V_{CE}$ = -2V ,  $I_{C}$ = -1A)
- · Low Saturation Voltage-
  - :  $V_{CE(sat)} = -0.3V(Max) @ (I_C = -3A, I_B = -0.15A)$
- · High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

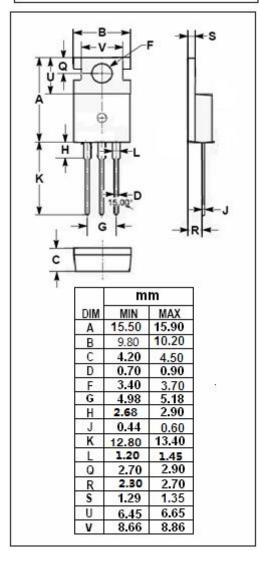


### **APPLICATIONS**

 Developed for use in switching power supplies, DC/DC converters, motor drivers, solenoid drivers, and other low-voltage power supply devices, as well as for highcurrent switching.

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-150	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-100	V	
$V_{EBO}$	Emitter-Base Voltage	-7.0	V	
Ic	Collector Current-Continuous	-5.0	Α	
Ісм	Collector Current-Pulse	-10	Α	
$I_{B}$	Base Current-Continuous	-2.5	Α	
P <sub>T</sub>	Total Power Dissipation @T <sub>C</sub> =25℃	30	W	
	Total Power Dissipation @T <sub>a</sub> =25°C	2.0		
TJ	Junction Temperature	150 °C		
T <sub>stg</sub>	Storage Temperature -55~150		$^{\circ}$	





# **isc Silicon PNP Power Transistor**

2SA1644

### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE</sub> (sat)-1	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -3A; I <sub>B</sub> = -0.15A			-0.3	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -4A; I <sub>B</sub> = -0.2A			-0.5	V
V <sub>BE(sat)-1</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -3A; I <sub>B</sub> = -0.15A			-1.2	V
V <sub>BE(sat)-2</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -4A; I <sub>B</sub> = -0.2A			-1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -100V; I <sub>E</sub> = 0			-10	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-10	μА
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -0.5A ; V <sub>CE</sub> = -2V	100			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -1.0A ; V <sub>CE</sub> = -2V	100		400	
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = -3.0A ; V <sub>CE</sub> = -2V	60			

### h<sub>FE-2</sub> Classifications

M	L	к
100-200	150-300	200-400

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